

Abstract of the Disclosure

Disclosed is a semiconductor device capable of reducing
5 parasitic capacitance and a method thereof, the method including the
steps of depositing sequentially an inorganic silicon oxide layer and
a low dielectric constant organic silicon oxide layer on a substrate,
forming a partial trench with a predetermined depth in the organic
silicon oxide layer by patterning, oxygenating an inner wall of the
10 partial trench, and forming a trench by etching the partial trench
with hydrofluoric acid (HF).